
EE230-02 RFIC II

Fall 2018

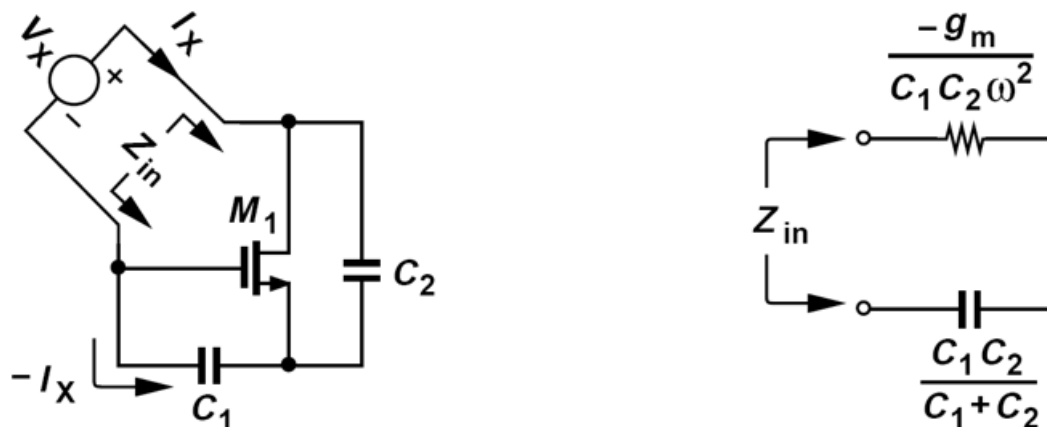
Lecture 14: Oscillators 3

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ENG-259

Midterm Exam

- **Oct. 16, Tuesday 4:30 PM**
- **One-page Aid sheet on Front side only allowed**
- **Bring a copy of your Aid sheet**
 - **Write your name and submit it for extra 5 points**
- **Bring your Calculator**

How Can a Circuit Present a Negative Input Resistance?



$$-\frac{I_X}{C_1 s} + V_X = \left(I_X + I_X \frac{g_m}{C_1 s} \right) \frac{1}{C_2 s}$$

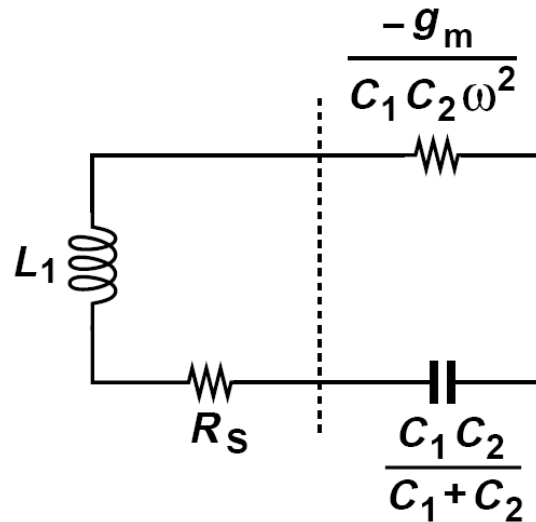
$$\frac{V_X}{I_X}(s) = \frac{1}{C_1 s} + \frac{1}{C_2 s} + \frac{g_m}{C_1 C_2 s^2}$$

$$\frac{V_X}{I_X}(j\omega) = \frac{1}{jC_1 \omega} + \frac{1}{jC_2 \omega} - \frac{g_m}{C_1 C_2 \omega^2}$$

➤ The negative resistance varies with frequency.

Connection of Lossy Inductor to Negative-Resistance Circuit

- Connect an inductor to the negative-resistance port to create a resonant tank



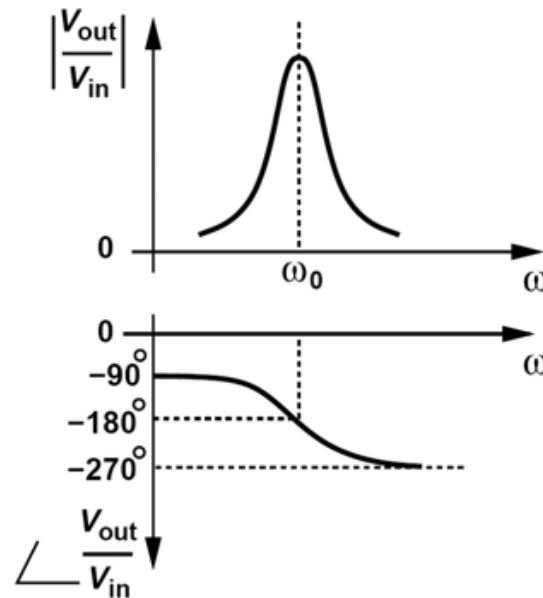
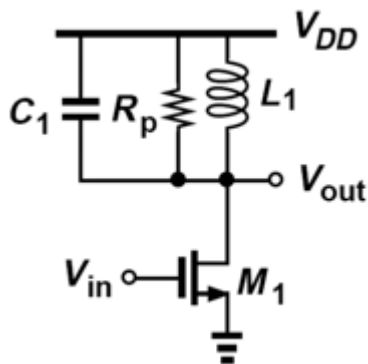
$$R_S = \frac{g_m}{C_1 C_2 \omega^2}$$

$$\omega_{osc} = \frac{1}{\sqrt{L_1 \frac{C_1 C_2}{C_1 + C_2}}}$$

Tuned Oscillator

Negative-feedback oscillatory system using “LC-tuned” amplifier stages

Can this circuit oscillate if its input and output are shorted?
NO!



At very low frequencies, L_1 dominates the load and

$$\frac{V_{out}}{V_{in}} \approx -g_m L_1 s$$

$|V_{out}/V_{in}|$ is very small and $\angle(V_{out}/V_{in})$ remains around -90°

At the resonance frequency

$$\frac{V_{out}}{V_{in}} = -g_m R_p$$

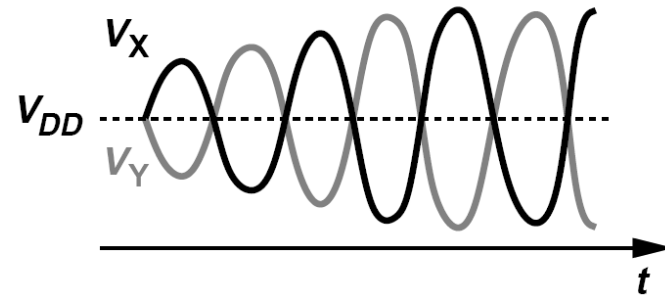
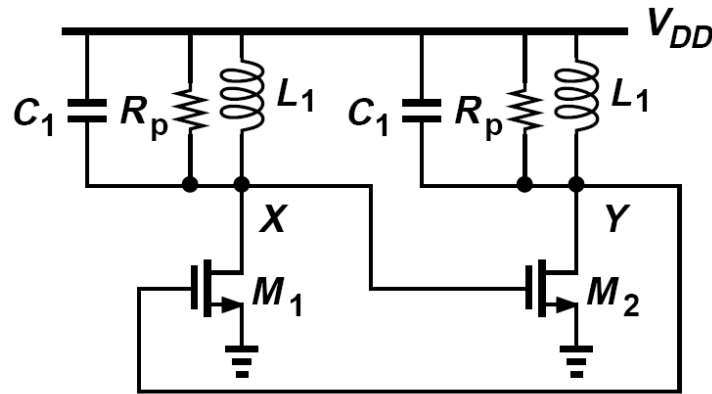
The phase shift from the input to the output is thus equal to -180°

At very high frequencies

$$\frac{V_{out}}{V_{in}} \approx -g_m \frac{1}{C_1 s}$$

$|V_{out}/V_{in}|$ diminishes $\angle(V_{out}/V_{in})$ approaches -270°

Cascade of Two Tuned Amplifiers in Feedback Loop

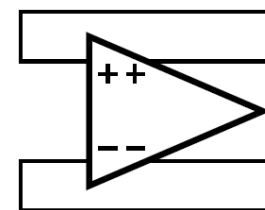
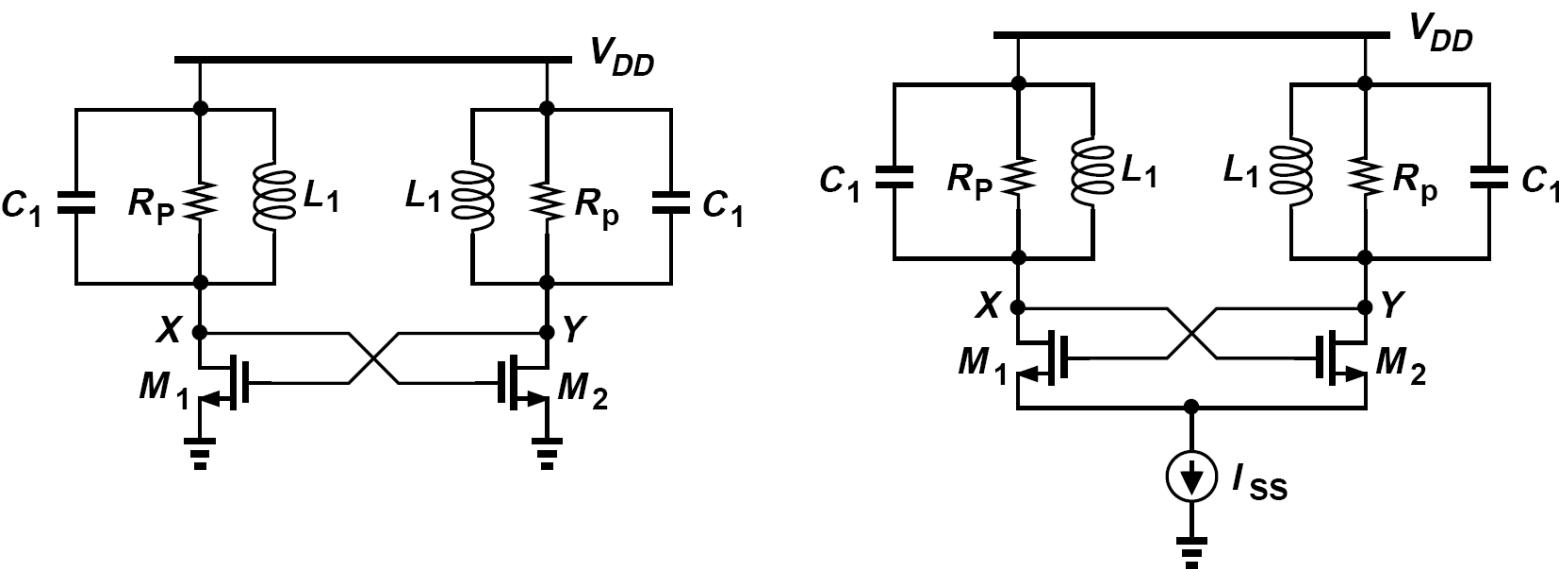


$$(g_m R_p)^2 \geq 1$$

A unique attribute of inductive loads

- Peak voltages above the supply
- The growth of V_X and V_Y ceases when M_1 and M_2 enter the triode region

Cross-Coupled Oscillator



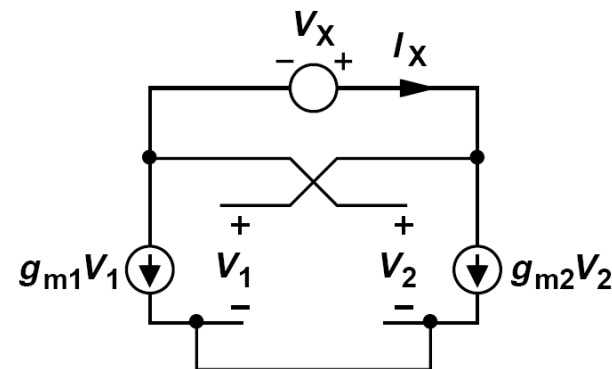
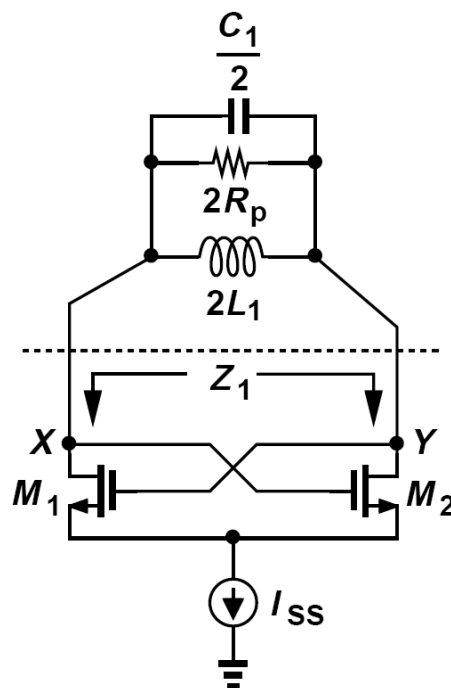
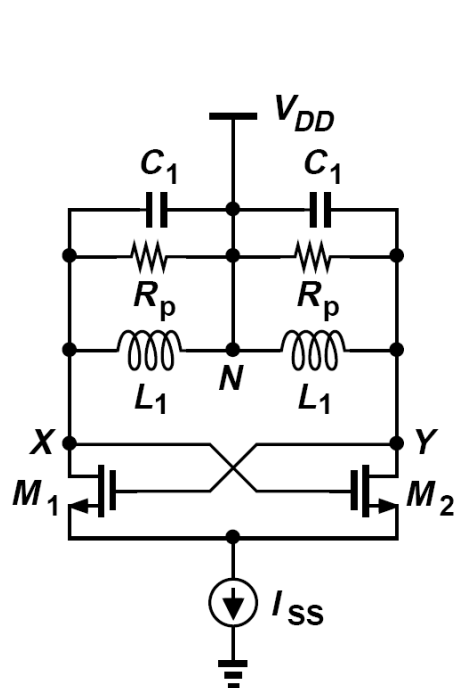
$$\omega_{osc} = \frac{1}{\sqrt{L_1(C_{GS2} + C_{DB1} + 4C_{GD} + C_1)}}$$

Left circuit suffers from poorly-defined bias currents.

Middle circuit is more robust and can be viewed as an inductively-loaded differential pair with positive feedback.

$$V_{XY} \approx \frac{4}{\pi} I_{SS} R_p$$

One-Port View of Cross-Coupled Oscillator



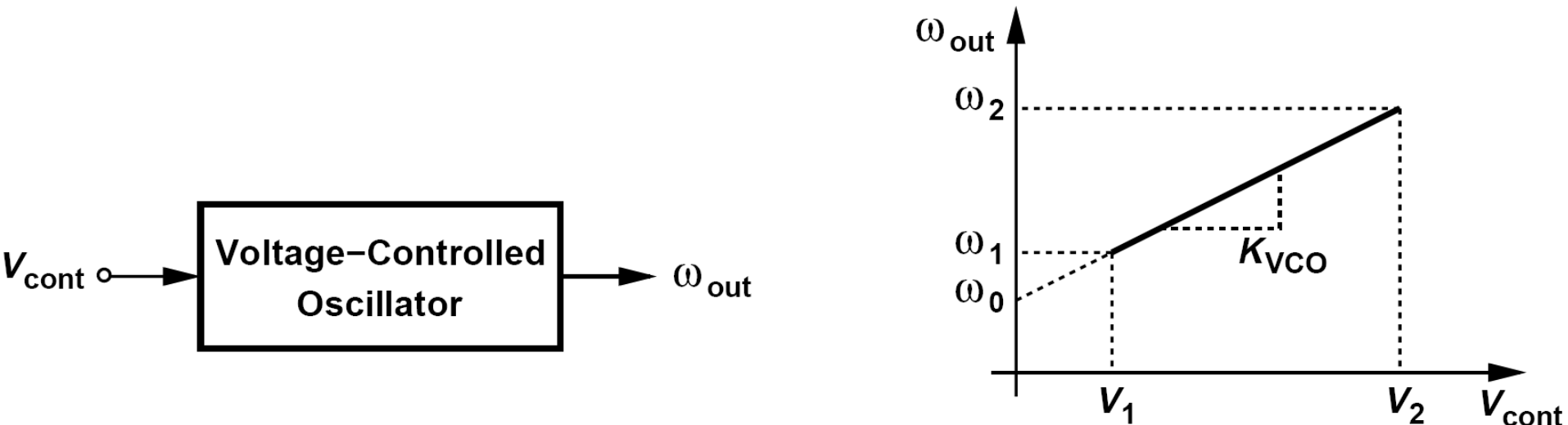
$$I_X = -g_{m1}V_1 = g_{m2}V_2 \quad \Rightarrow \quad \frac{V_X}{I_X} = - \left(\frac{1}{g_{m1}} + \frac{1}{g_{m2}} \right)$$

For $g_{m1} = g_{m2} = g_m$ $\frac{V_X}{I_X} = -\frac{2}{g_m}$

For oscillation to occur,
the negative resistance must cancel the loss of the tank:

$$\frac{2}{g_m} \leq 2R_p \quad \Rightarrow \quad g_m R_p \geq 1$$

Voltage-Controlled Oscillators: Characteristic

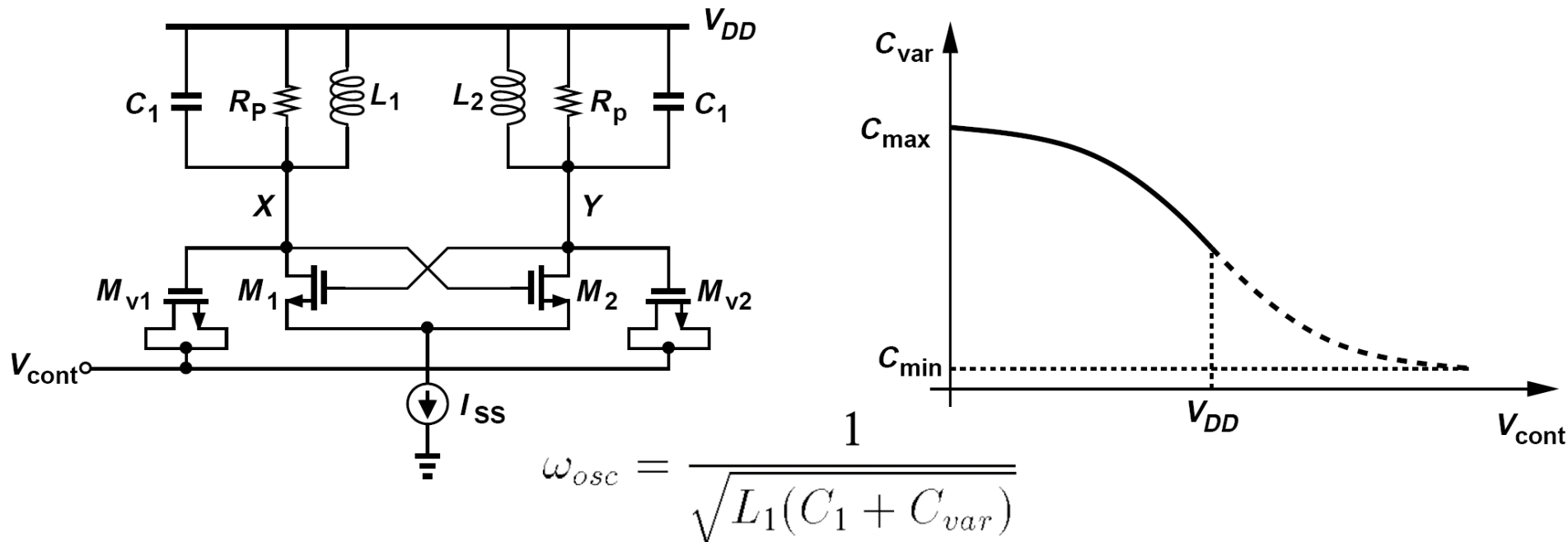


$$\omega_{out} = K_{VCO} V_{cont} + \omega_0$$

- The frequency varies from ω_1 to ω_2 (the required tuning range) as the control voltage, V_{cont} , goes from V_1 to V_2
- The slope, K_{VCO} , is called the “gain” or “sensitivity” of the VCO and expressed in rad/s/V.

VCO Using MOS Varactors

- Since it is difficult to vary the inductance electronically, we vary the capacitance by means of a varactor.
- MOS varactors are more commonly used than *pn* junctions, especially in low-voltage design.



- First, the varactors are stressed for part of the period if V_{cont} is near ground and V_X (or V_Y) rises significantly above V_{DD} .
- Second, only about half of $C_{max} - C_{min}$ is utilized in the tuning.

Varactors

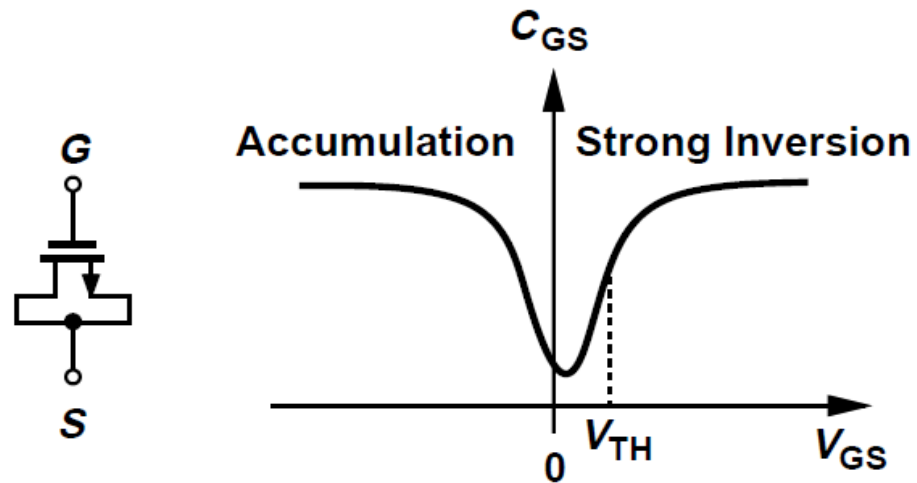
Varactor is a voltage-dependent capacitor.

Two important attributes of varactor design become critical in oscillator design

- **The capacitance range i.e. ratio of maximum to minimum capacitance that varactor can provide.**
- **The quality factor of the varactor.**

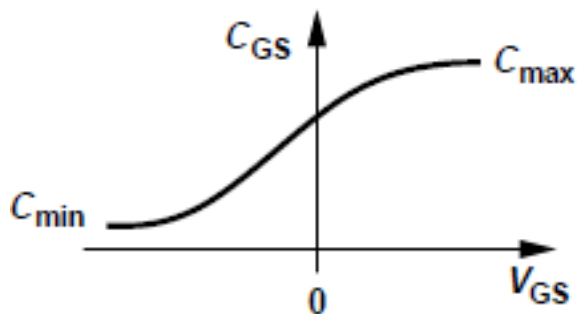
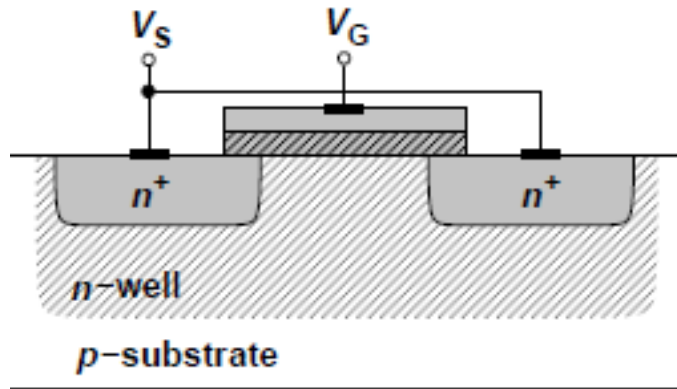
MOS Varactors

Regular MOS device:



Variation of gate capacitance with V_{GS}

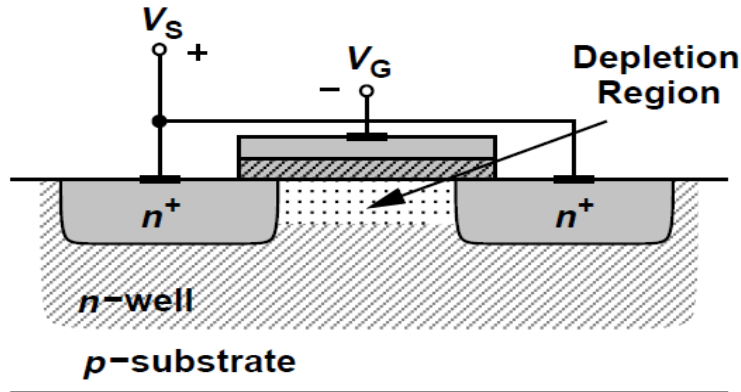
Accumulation Mode MOS Varactor



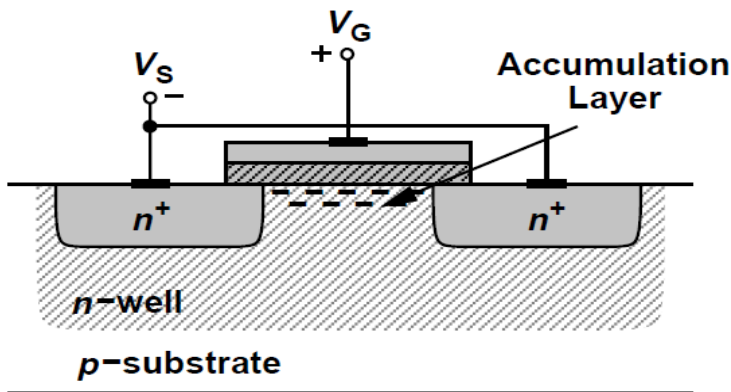
C/V characteristics of varactor

- Accumulation-mode MOS varactor is obtained by placing an NMOS inside an nwell .
- The variation of capacitance with V_{gs} is monotonic.
- The C/V characteristics scale well with scaling in technology.
- Unlike PN junction varactor this structure can operate with positive and negative bias so as to provide maximum tuning range.

Accumulation Mode MOS Varactor Operation



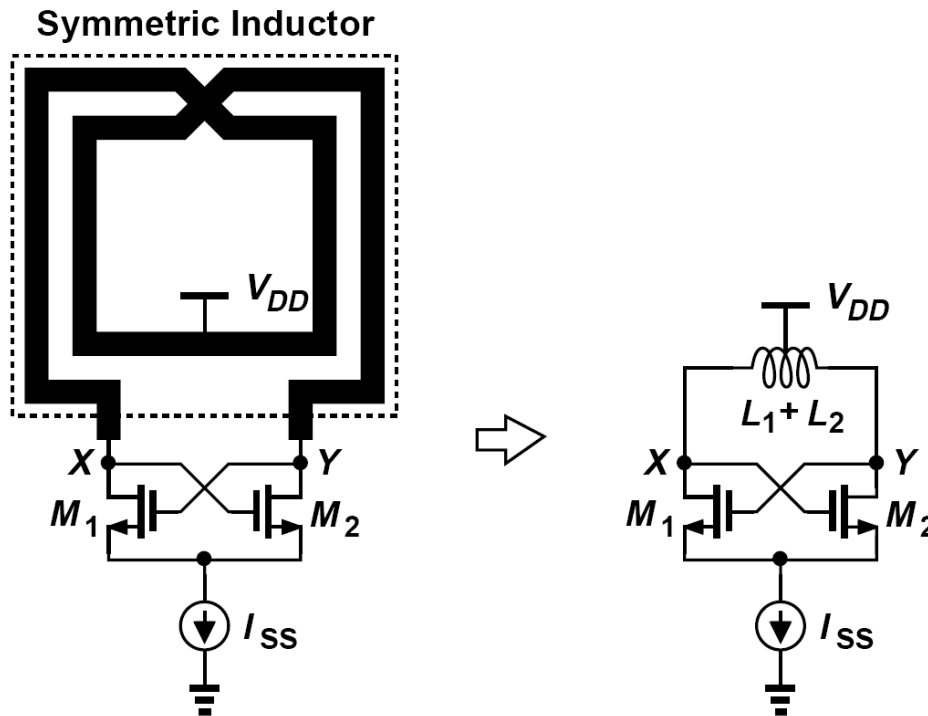
- $V_G < V_S$
- Depletion region is formed under gate oxide.
- Equivalent capacitance is the series combination of gate capacitance and depletion capacitance.



- $V_G > V_S$
- Formation of channel under gate oxide.

Oscillator Using Symmetric Inductor

- Symmetric spiral inductors excited by differential waveforms exhibit a higher Q than their single-ended counterparts.



$$L_1 = L_2 = 1 \text{ nH}$$
$$Q = 10 \text{ at } 10 \text{ GHz}$$

What is the minimum required transconductance of M_1 and M_2 to guarantee start-up?

$$g_{m1,2} \geq (630 \, \Omega)^{-1}$$

Tuning Range Limitations

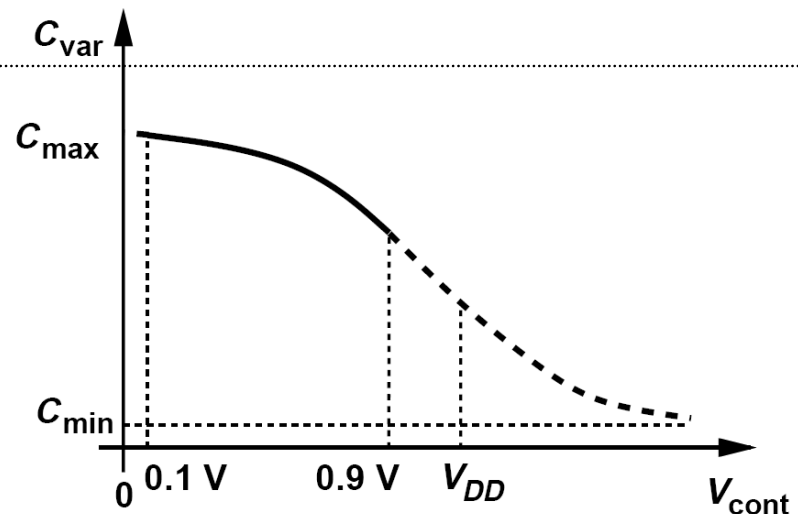
If $C_{var} \ll C_1$, then

$$\omega_{osc} \approx \frac{1}{\sqrt{L_1 C_1}} \left(1 - \frac{C_{var}}{2C_1} \right)$$

If the varactor capacitance varies from C_{var1} to C_{var2} , then the tuning range is given by

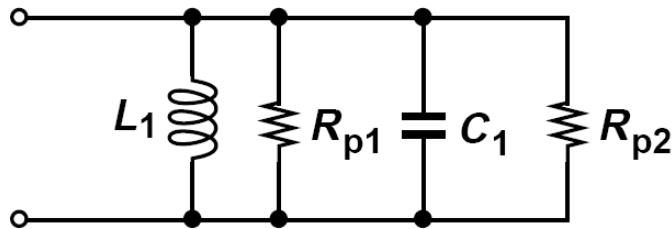
$$\Delta\omega_{osc} \approx \frac{1}{\sqrt{L_1 C_1}} \frac{C_{var2} - C_{var1}}{2C_1}$$

➤ Another limitation on $C_{var2} - C_{var1}$ arises from the available control voltage range of the oscillator, V_{cont} .



Effect of Varactor Q: Tank Consisting of Lossy Inductor and Capacitor

A lossy inductor and a lossy capacitor form a parallel tank. Determine the overall Q in terms of the quality factor of each.



$$Q_L = \frac{R_{p1}}{L_1 \omega}$$
$$Q_C = R_{p2} C_1 \omega$$

Merging R_{p1} and R_{p2} yields the overall Q:

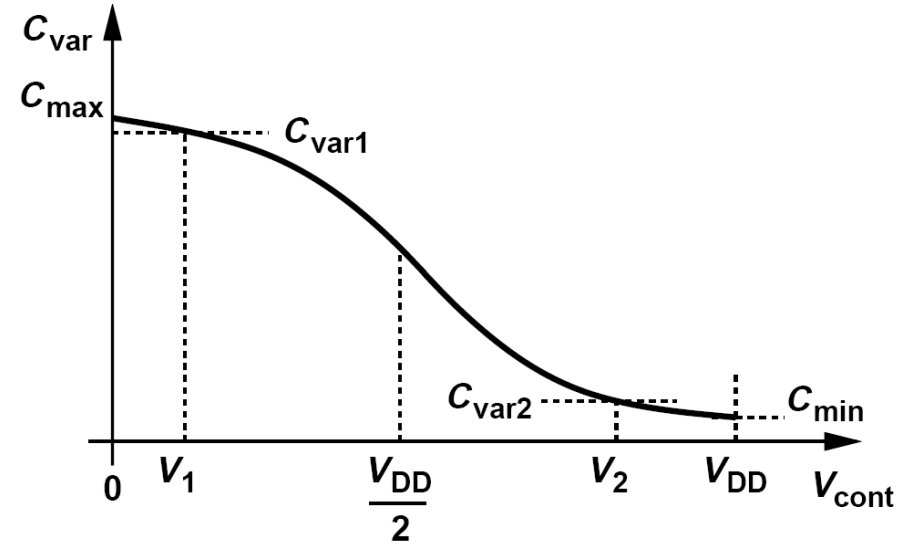
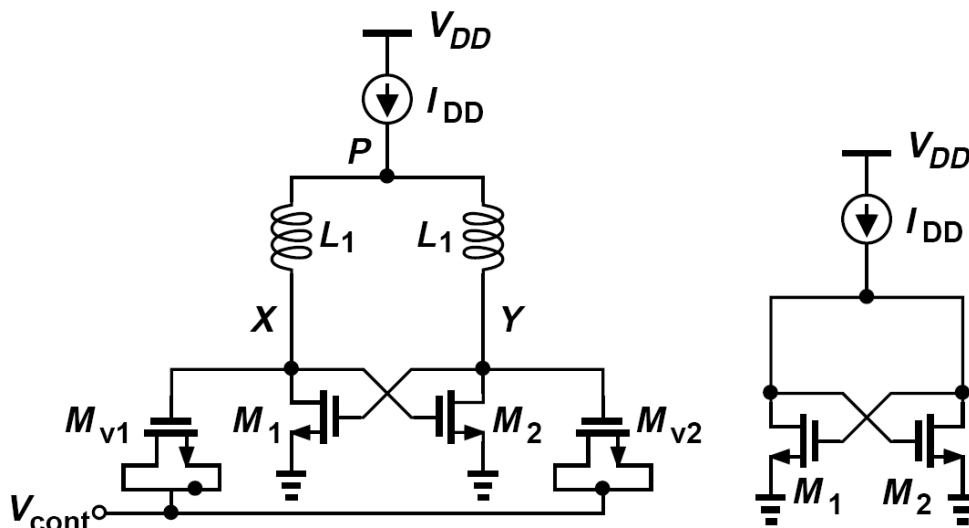
$$\begin{aligned} Q_{tot} &= \frac{R_{p1} R_{p2}}{R_{p1} + R_{p2}} \cdot \frac{1}{L_1 \omega} \\ &= \frac{1}{\frac{L_1 \omega}{R_{p1}} + \frac{L_1 \omega}{R_{p2}}} \\ &= \frac{1}{\frac{L_1 \omega}{R_{p1}} + \frac{1}{R_{p2} C_1 \omega}} \end{aligned}$$



$$\frac{1}{Q_{tot}} = \frac{1}{Q_L} + \frac{1}{Q_C}$$

LC VCOs with Wide Tuning Range: VCOs with Continuous Tuning

➤ We seek oscillator topologies that allow both positive and negative (average) voltages across the varactors, utilizing almost the entire range from C_{min} to C_{max} .



The CM level at X & Y:

$$V_{GS1,2} = \sqrt{\frac{I_{DD}}{\mu_n C_{ox} (W/L)}} + V_{TH}$$

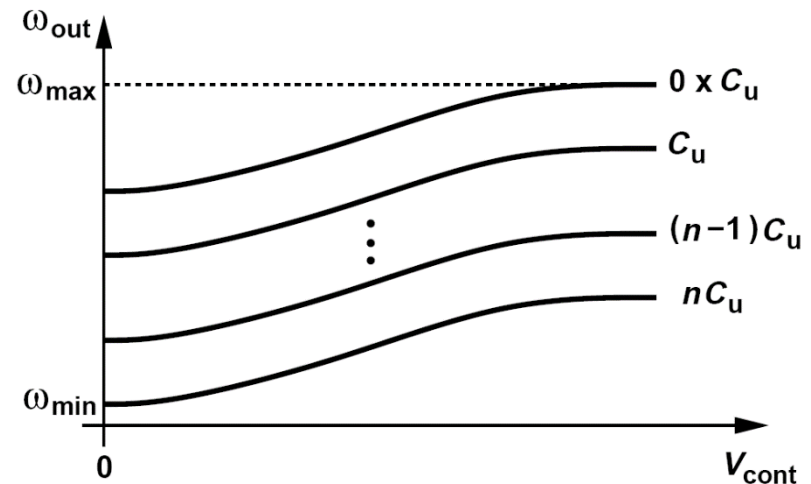
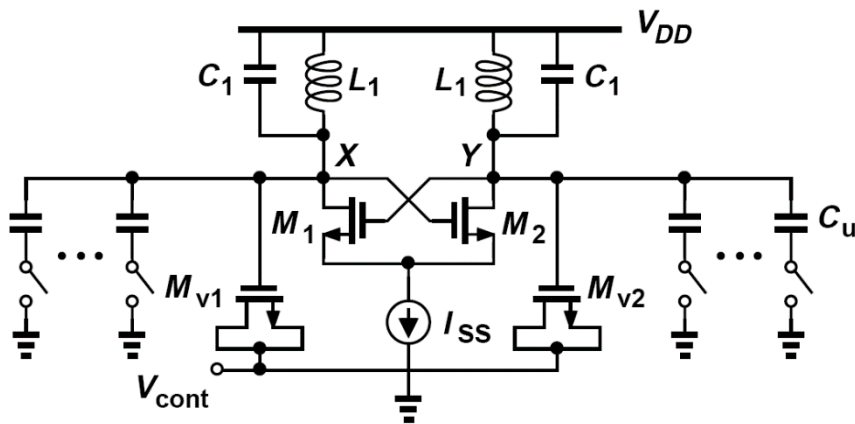
Select the transistor dimensions such that the CM level is approximately equal to $V_{DD}/2$.

As V_{cont} varies from 0 to V_{DD} ,

the gate-source voltage of the varactors, $V_{GS,var}$ goes from $+V_{DD}/2$ to $-V_{DD}/2$,

Discrete Tuning

- In applications where a substantially wider tuning range is necessary, “discrete tuning” may be added to the VCO so as to achieve a capacitance range well beyond C_{max}/C_{min} of varactors.



$$\omega_{min} = \frac{1}{\sqrt{L_1(C_1 + C_{max} + nC_u)}}$$

$$\omega_{max} = \frac{1}{\sqrt{L_1(C_1 + C_{min})}}$$